

KTD1302
Rev.E Mar.-2016

TO-92 NPN Silicon NPN transistor in a TO-92 Plastic Package.

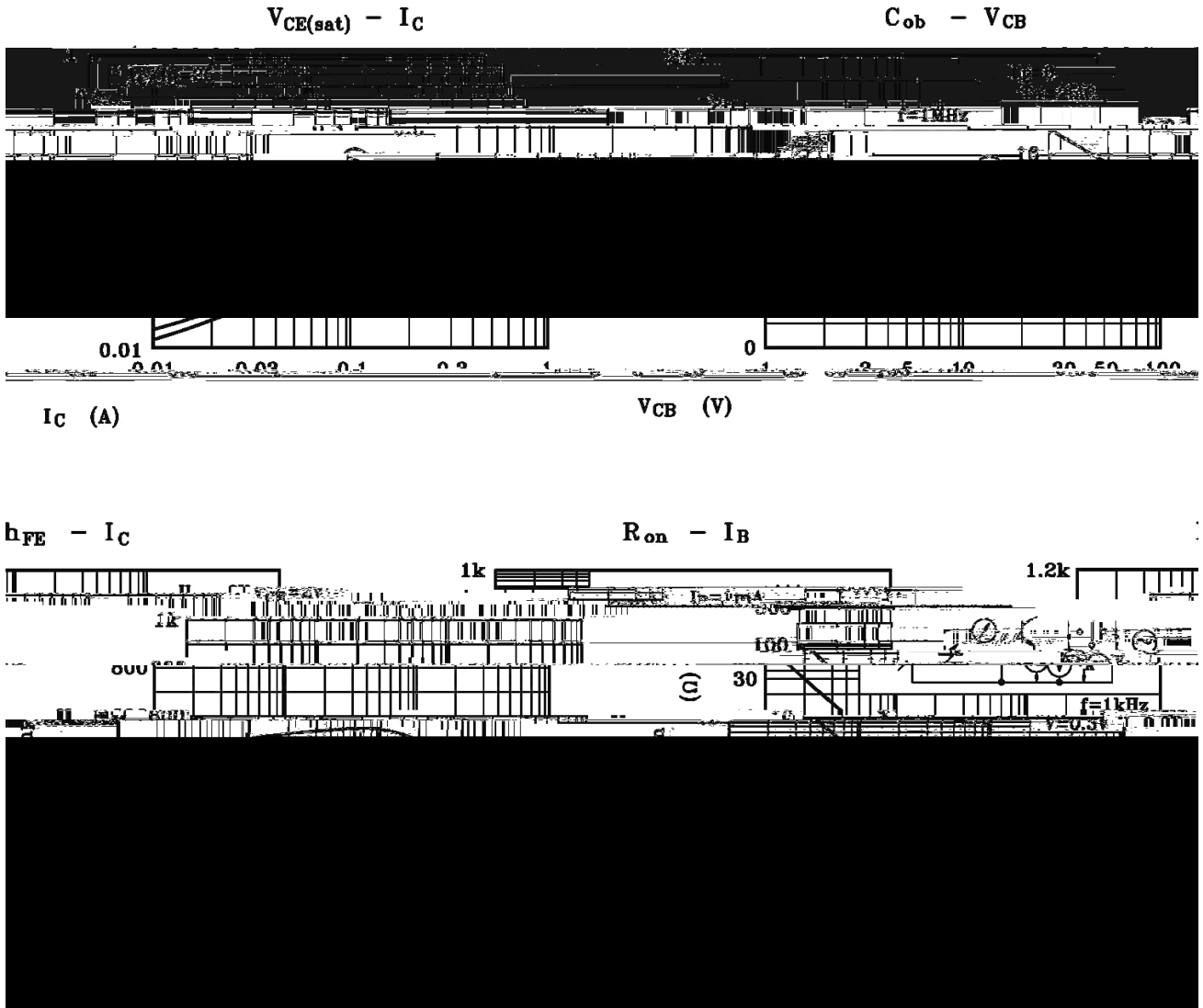
: $R_{on}=0.6$ (Typ.)($I_B=1.0mA$)

Low on Resistance: $R_{on}=0.6$ (Typ.)($I_B=1.0mA$).

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{76C}	25	V
Collector to Emitter Voltage	V_{CEO}	20	V
Emitter to Base Voltage	V_{EBO}	9.0	V
Collector Current - Continuous	I_C	300	mA
Base Current – Continuous	I_B	30	mA
Collector Power Dissipation	P_C	625	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cut-Off Current	I_{CBO}	$V_{CB}=25V$ $I_E=0$			0.1	μA
Emitter Cut-Off Current	I_{EBO}	$V_{EB}=9.0V$ $I_C=0$			0.1	μA
DC Current Gain	h_{FE}	$V_{CE}=2.0V$ $I_C=4.0mA$	200		800	
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=100mA$ $I_B=10mA$			0.25	V

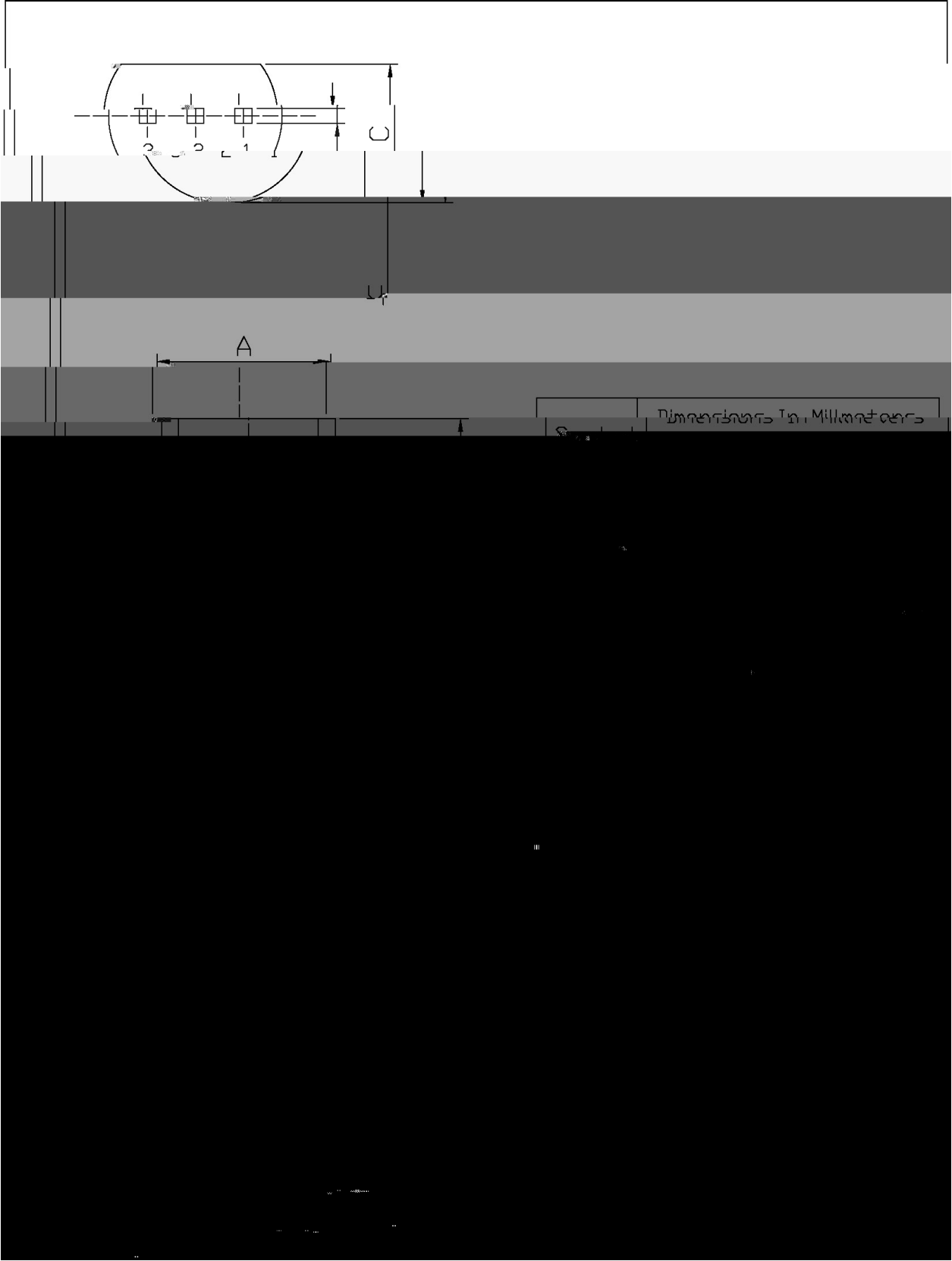
/ Electrical Characteristic Curve



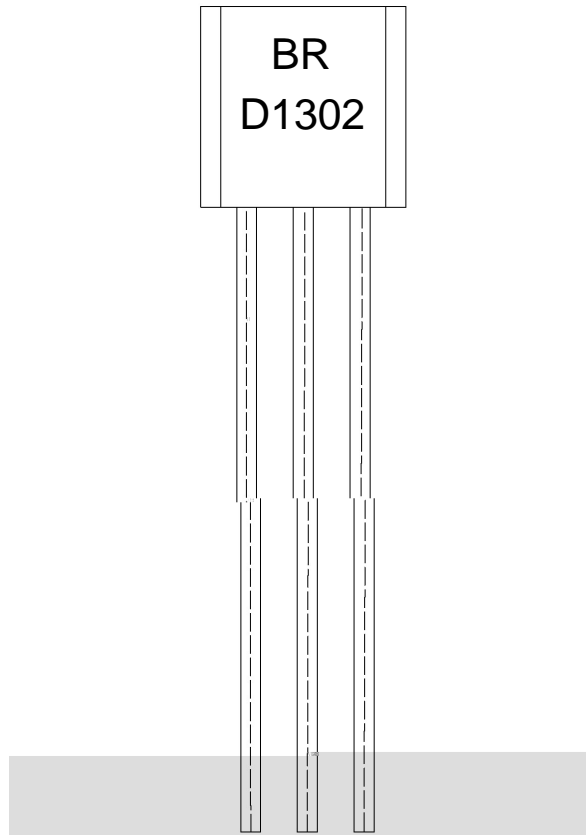
/ Package Dimensions

T0-92

Unit: mm



/ Marking Instructions



BR:

D1302

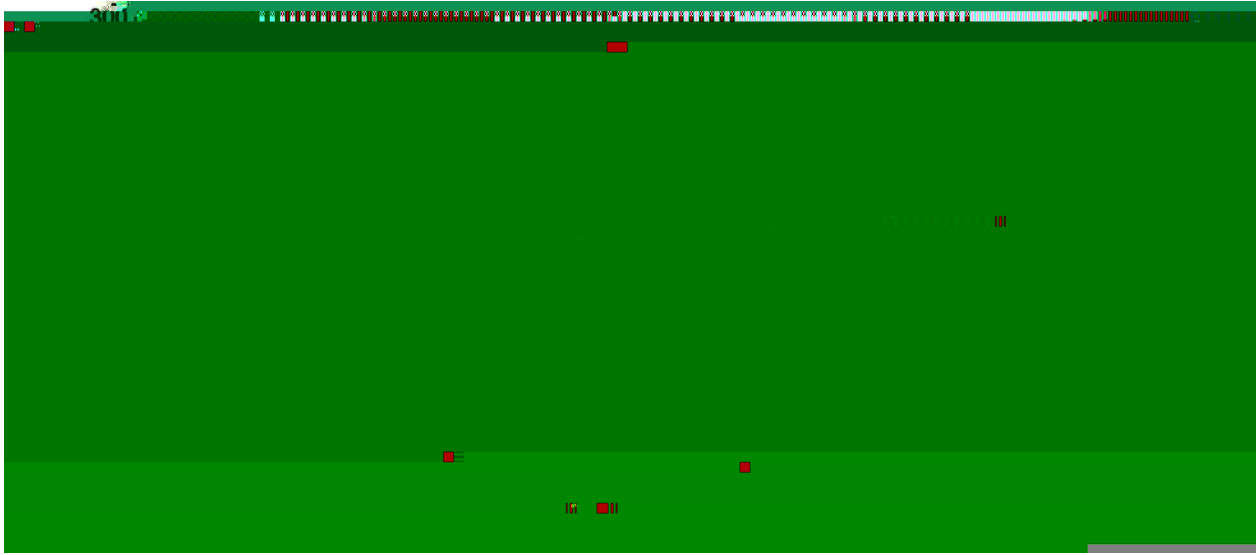
Note:

BR: Company Code.

D1302: Product Type.

****: Lot No. Code,code change with Lot No.

() / Temperature Profile for Dip Soldering(Pb-Free)



Note:

- | | | | | | |
|---|-------|-----|-----------|--------|---|
| 1 | 25 | 150 | 60 | 90sec; | 1.Preheating:25~150 , Time:60~90sec. |
| 2 | 255±5 | | 5±0.5sec; | | 2.Peak Temp.:255±5 , Duration:5±0.5sec. |
| 3 | | 2 | 10 | /sec. | 3. Cooling Speed: 2~10 /sec. |

/ Resistance to Soldering Heat Test Conditions

270±5 10±1 sec. Temp:270±5 Time:10±1 sec

/ Packaging SPEC.

/ BULK

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm3)		
	只袋	袋盒	只盒	盒箱	只箱	袋	盒	箱

/ AMMO

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm3)	
	只纸带	纸带盒	纸带层盒	盒箱	只箱	盒	箱
						小箱	大箱

/ Notices